

# 2N3903\_D26Z Datasheet

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DiGi Electronics Part Number	2N3903_D26Z-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	2N3903_D26Z
Description	TRANS NPN 40V 0.2A TO92-3
Detailed Description	Bipolar (BJT) Transistor NPN 40 V 200 mA 625 mW Through Hole TO-92-3



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RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

2N3903\_D26Z

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

40 V

Current - Collector Cutoff (Max):

-

Power - Max:

625 mW

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

TO-226-3, TO-92-3 (TO-226AA) Formed Leads

Base Product Number:

2N3903

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

200 mA

Vce Saturation (Max) @ Ib, Ic:

300mV @ 5mA, 50mA

DC Current Gain (hFE) (Min) @ Ic, Vce:

50 @ 10mA, 1V

Frequency - Transition:

-

Mounting Type:

Through Hole

Supplier Device Package:

TO-92-3

## Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

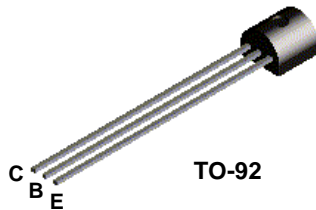
REACH Unaffected

HTSUS:

8541.21.0095



## 2N3903



### NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CB0</sub>	Collector-Base Voltage	60	V
V <sub>EB0</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3903	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

## NPN General Purpose Amplifier

(continued)

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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## OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	6.0		V
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
$I_{BL}$	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA

## ON CHARACTERISTICS\*

$h_{FE}$	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 0.1 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 100 \text{ mA}$	20 35 50 30 15	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.2 0.3	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V V

## SMALL SIGNAL CHARACTERISTICS

$C_{ob}$	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 100 \text{ kHz}$		4.0	pF
$C_{ib}$	Input Capacitance	$V_{EB} = 0.5 \text{ V}, f = 100 \text{ kHz}$		8.0	pF
$h_{re}$	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$	2.5		
$h_{fe}$	Small-Signal Current Gain	$V_{CE} = 10 \text{ V}, I_C = 1.0 \text{ mA}$	50	200	
$h_{ie}$	Input Impedance	$f = 1.0 \text{ kHz}$	1.0	8.0	k $\Omega$
$h_{re}$	Voltage Feedback Ratio		0.1	5.0	$\times 10^{-4}$
$h_{oe}$	Output Admittance		1.0	40	$\mu\text{mhos}$
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ } \mu\text{A},$ $R_S = 1.0 \text{ k}\Omega,$ $B_W = 10 \text{ Hz to } 15.7 \text{ kHz}$		6.0	dB

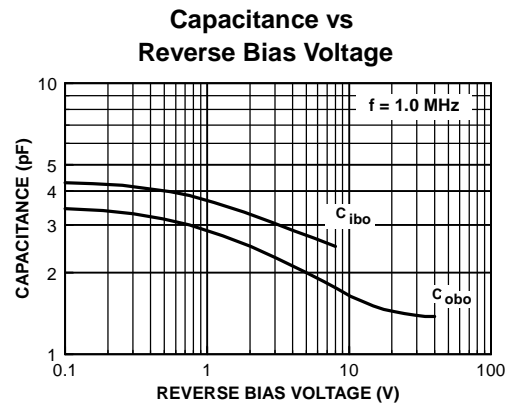
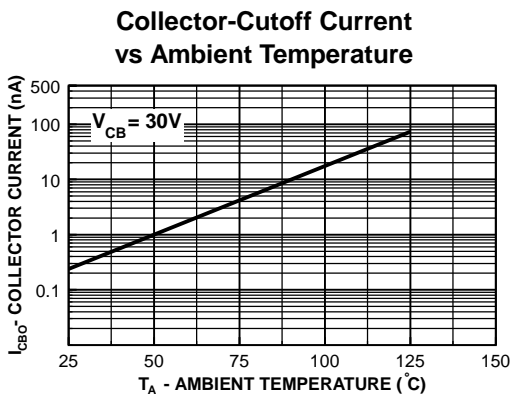
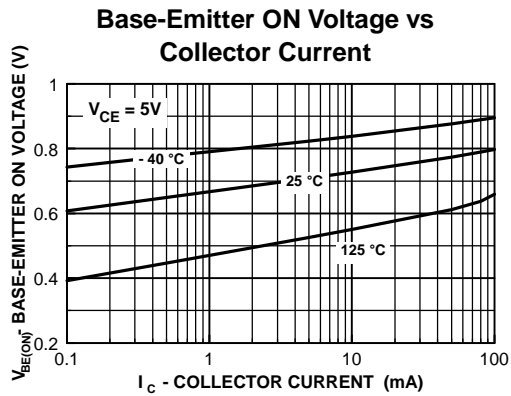
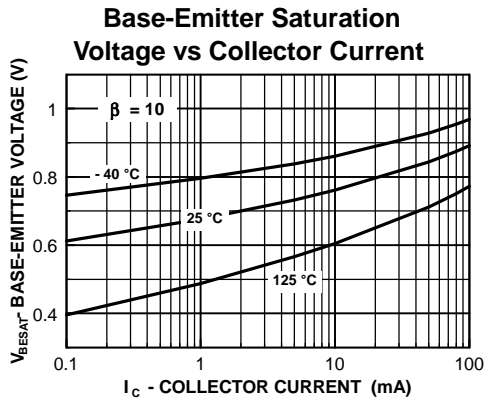
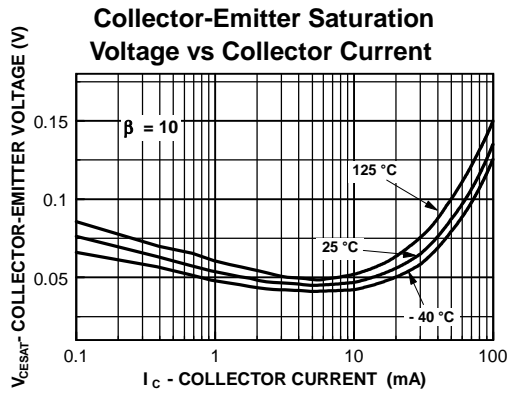
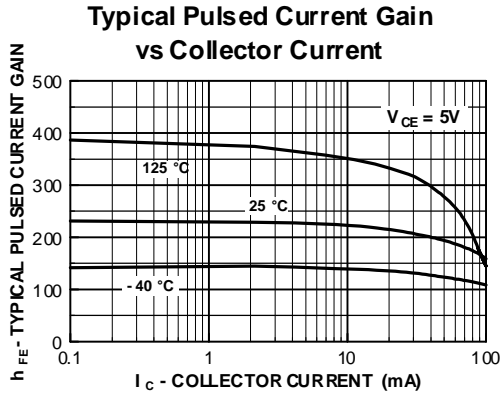
## SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA},$		35	ns
$t_r$	Rise Time	$I_{B1} = 1.0 \text{ mA}, V_{ob}(\text{off}) = 0.5 \text{ V}$		35	ns
$t_s$	Storage Time	$V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA}$		175	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		50	ns

\*Pulse Test: Pulse Width  $\leq 300 \text{ } \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

**NPN General Purpose Amplifier**  
(continued)

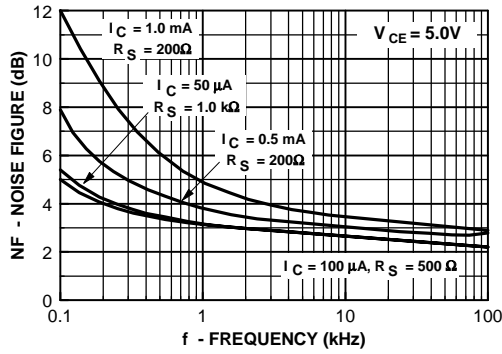
**Typical Characteristics**



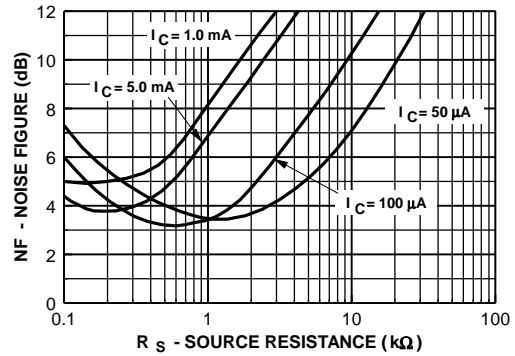
**NPN General Purpose Amplifier**  
(continued)

**Typical Characteristics** (continued)

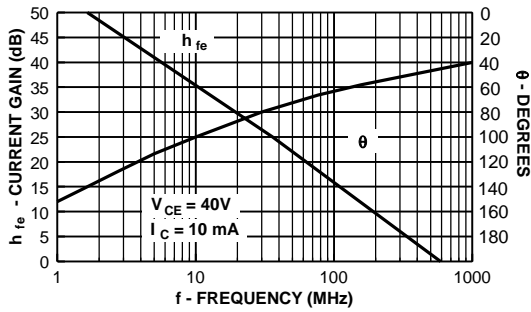
**Noise Figure vs Frequency**



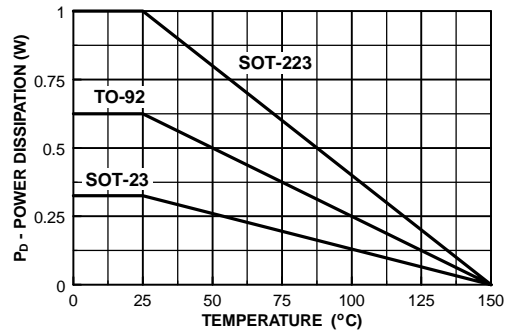
**Noise Figure vs Source Resistance**



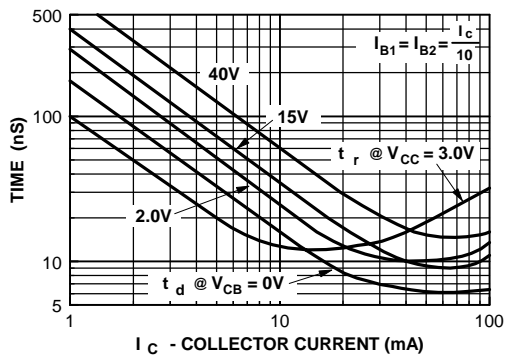
**Current Gain and Phase Angle vs Frequency**



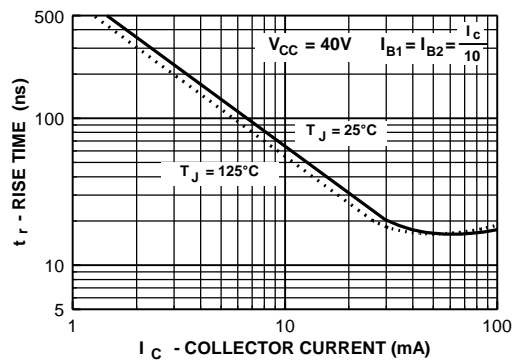
**Power Dissipation vs Ambient Temperature**



**Turn-On Time vs Collector Current**



**Rise Time vs Collector Current**

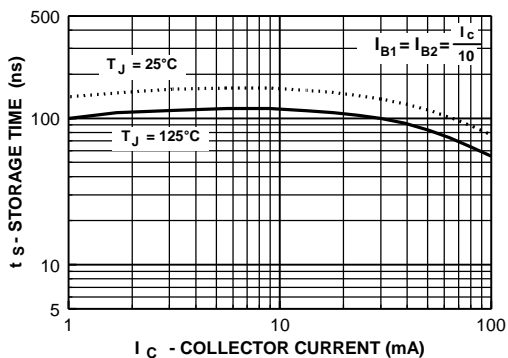


# NPN General Purpose Amplifier

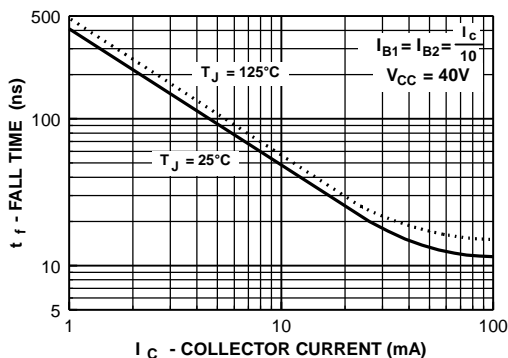
(continued)

## Typical Characteristics (continued)

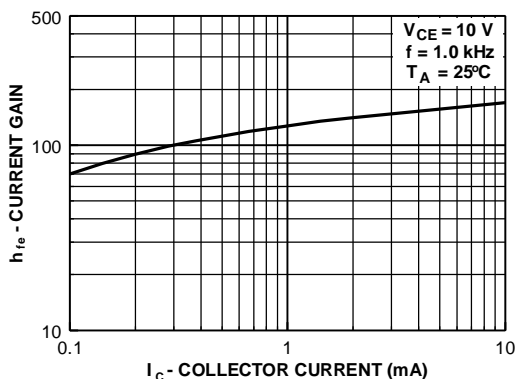
**Storage Time vs Collector Current**



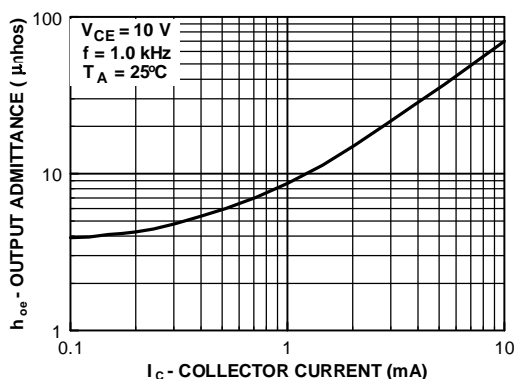
**Fall Time vs Collector Current**



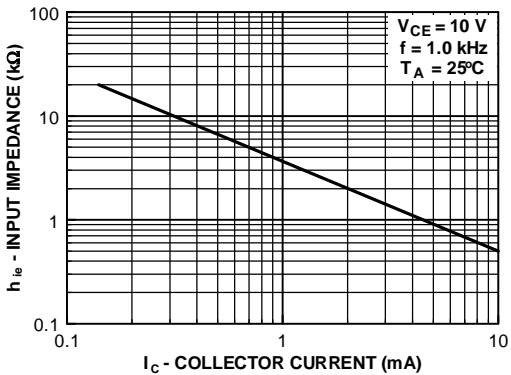
**Current Gain**



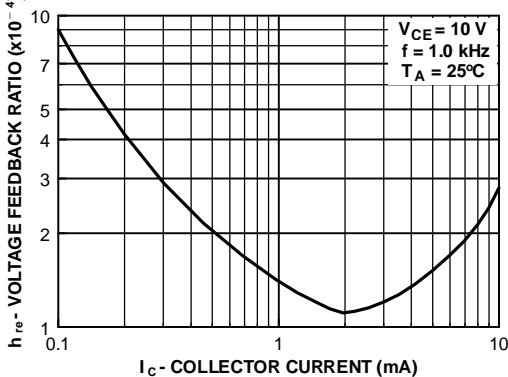
**Output Admittance**



**Input Impedance**



**Voltage Feedback Ratio**



## NPN General Purpose Amplifier

(continued)

2N3903

### Test Circuits

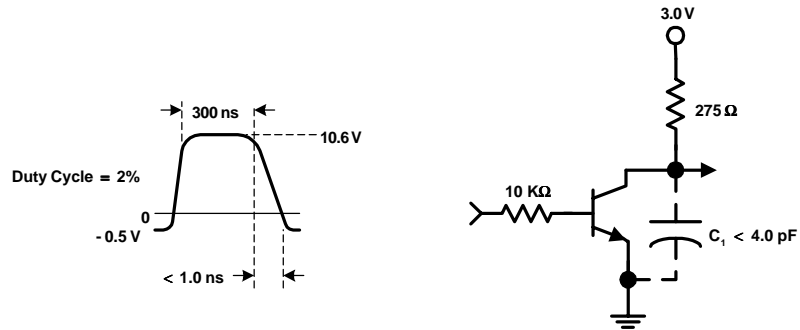


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

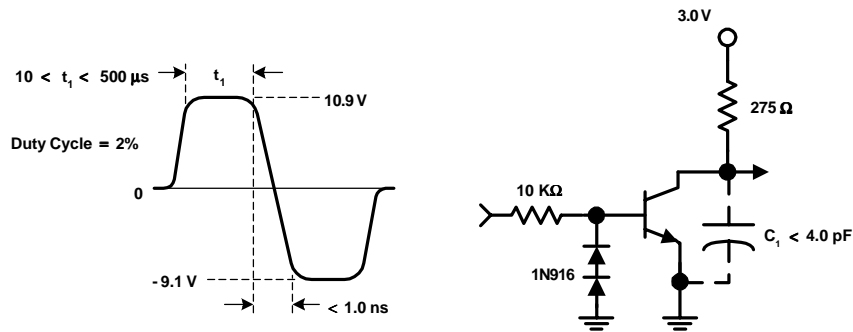


FIGURE 2: Storage and Fall Time Equivalent Test Circuit

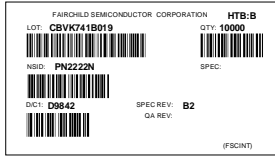




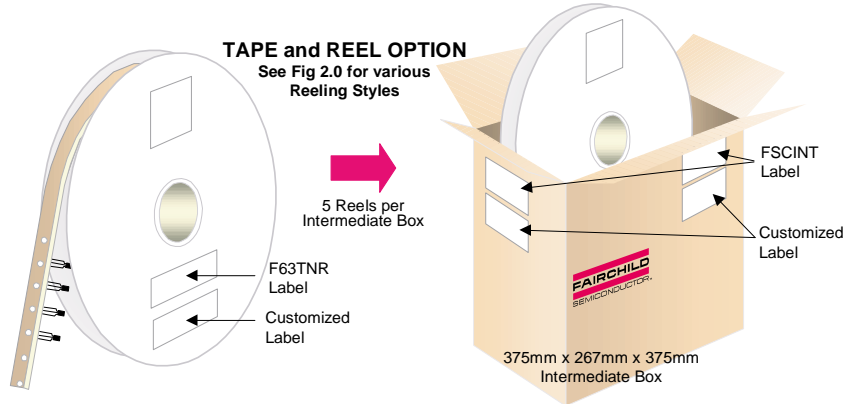
# TO-92 Tape and Reel Data

## TO-92 Packaging Configuration: Figure 1.0

FSCINT Label sample



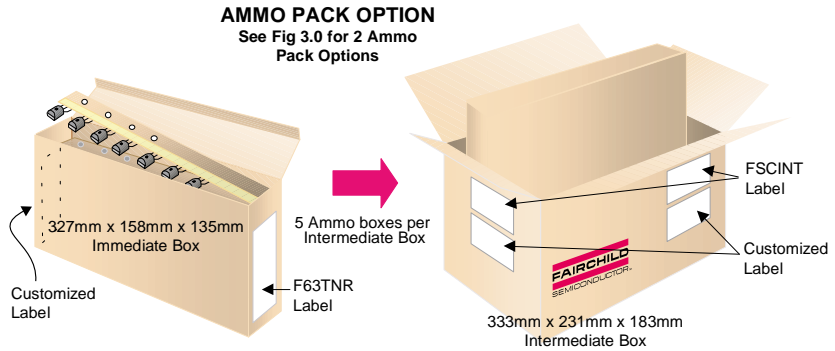
F63TNR Label sample



### TO-92 TNR/AMMO PACKING INFORMATION

Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	E	2,000	D27Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm  
 Reel weight with components = 1.04 kg  
 Ammo weight with components = 1.02 kg  
 Max quantity per intermediate box = 10,000 units

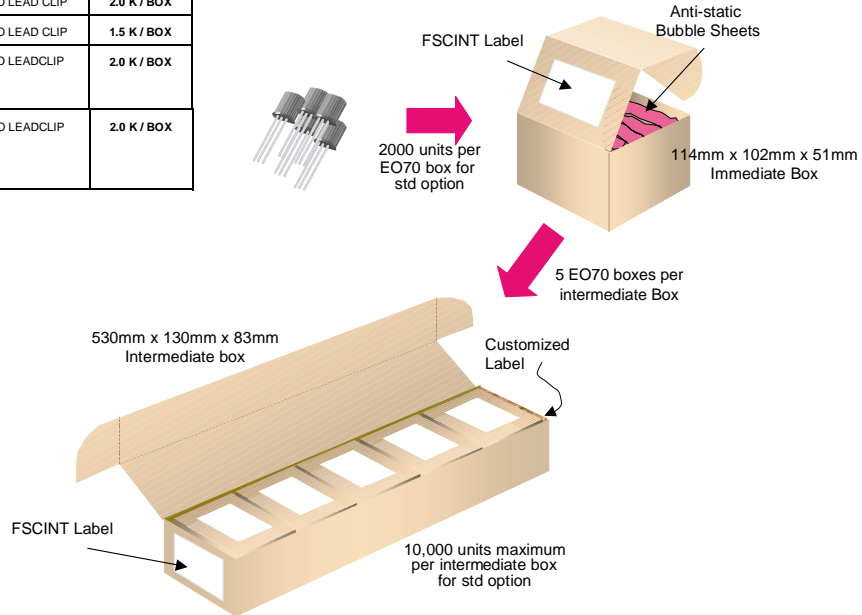


### (TO-92) BULK PACKING INFORMATION

EOL CODE	DESCRIPTION	LEADCLIP DIMENSION	QUANTITY
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0 K / BOX
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5 K / BOX
NO EOL CODE	TO-92 STANDARD STRAIGHT FOR: PKG 92, 94 (NON PROELECTRON SERIES), 96	NO LEADCLIP	2.0 K / BOX
L34Z	TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98	NO LEADCLIP	2.0 K / BOX

### BULK OPTION

See Bulk Packing Information table

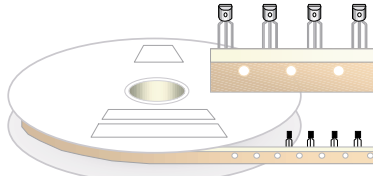


## TO-92 Tape and Reel Data, continued

### TO-92 Reeling Style

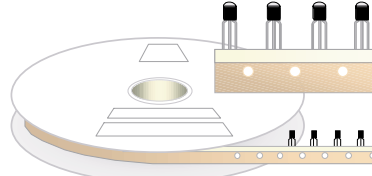
Configuration: Figure 2.0

#### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

#### Machine Option "E" (J)

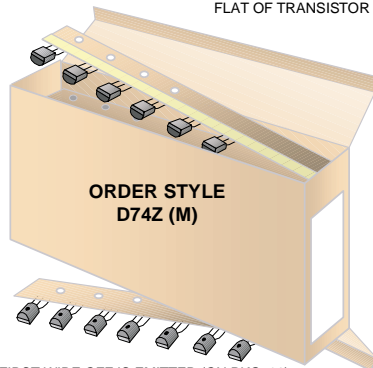


Style "E", D27Z, D71Z (s/h)

### TO-92 Radial Ammo Packaging

Configuration: Figure 3.0

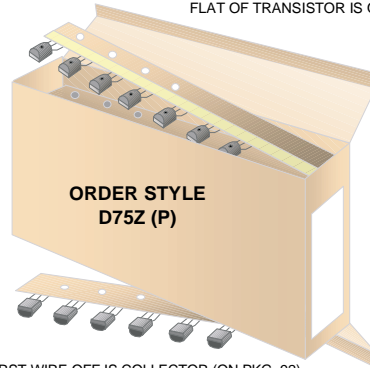
FIRST WIRE OFF IS COLLECTOR  
ADHESIVE TAPE IS ON THE TOP SIDE  
FLAT OF TRANSISTOR IS ON TOP



ORDER STYLE  
D74Z (M)

FIRST WIRE OFF IS EMITTER (ON PKG. 92)  
ADHESIVE TAPE IS ON BOTTOM SIDE  
FLAT OF TRANSISTOR IS ON BOTTOM

FIRST WIRE OFF IS EMITTER  
ADHESIVE TAPE IS ON THE TOP SIDE  
FLAT OF TRANSISTOR IS ON BOTTOM

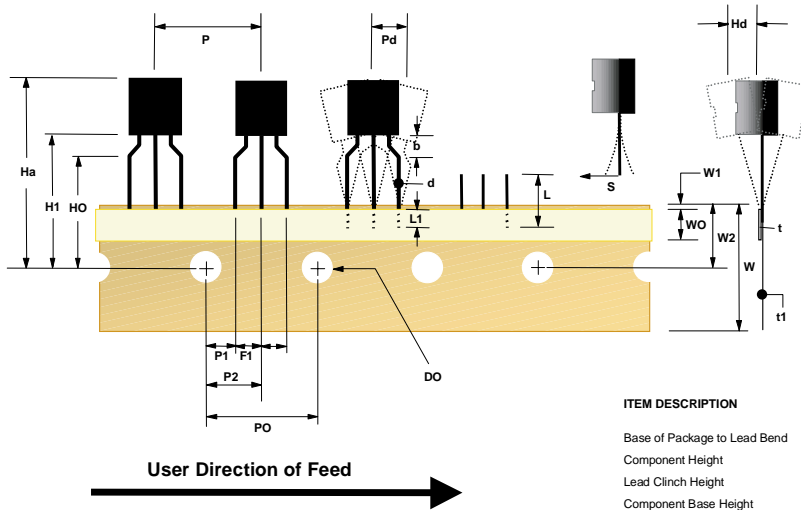


ORDER STYLE  
D75Z (P)

FIRST WIRE OFF IS COLLECTOR (ON PKG. 92)  
ADHESIVE TAPE IS ON BOTTOM SIDE  
FLAT OF TRANSISTOR IS ON TOP

## TO-92 Tape and Reel Data, continued

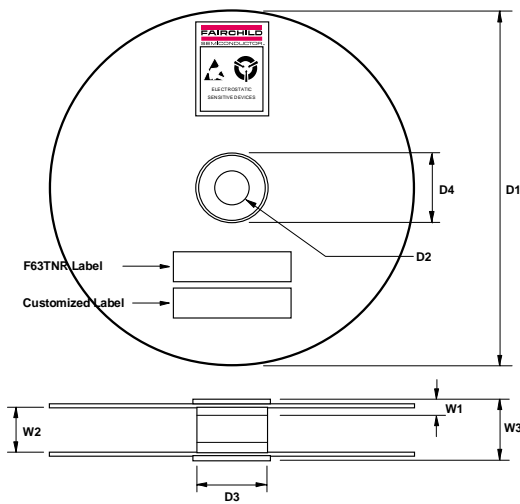
**TO-92 Tape and Reel Taping  
Dimension Configuration: Figure 4.0**



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment ( side/side )	Pd	0.040 (max)
Component Alignment ( front/back )	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0.010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note : All dimensions are in inches.

**TO-92 Reel  
Configuration: Figure 5.0**



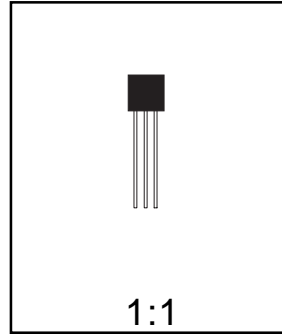
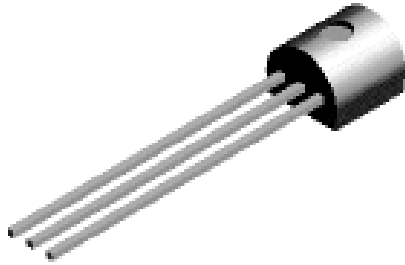
ITEM DESCRIPTION	SYMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are in inches

### TO-92 Package Dimensions



## TO-92 (FS PKG Code 92, 94, 96)



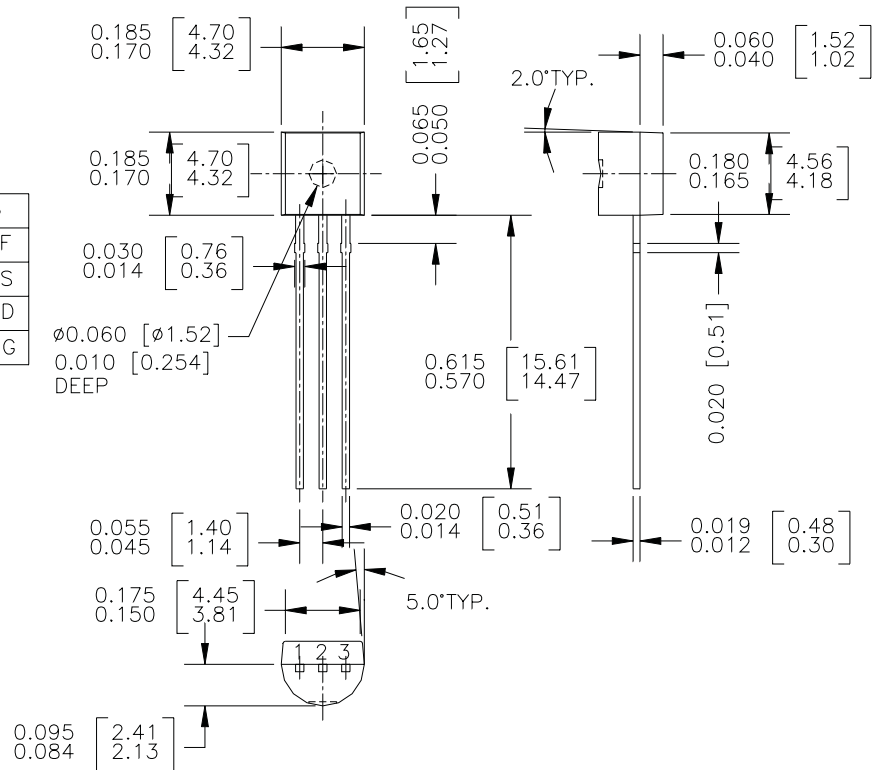
Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.1977

TO-92 (92,94,96)

PIN	92		94		96	
	B	F	B	F	B	F
1	E	D	E	D	B	S
2	B	S	C	G	E	D
3	C	G	B	S	C	G



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DOME <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	Quiet Series <sup>TM</sup>	
E <sup>2</sup> CMOS <sup>TM</sup>	MICROWIRE <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	
EnSigna <sup>TM</sup>	OPTOLOGIC <sup>TM</sup>	SMART START <sup>TM</sup>	
FACT <sup>TM</sup>	OPTOPLANAR <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
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FAST <sup>®</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -8	

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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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